

M/A-COM Products

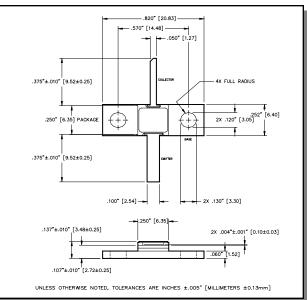
Released, 30 May 07

Radar Pulsed Power Transistor 25W, 1.2-1.4 GHz, 300µs Pulse, 10% Duty

Features

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V _{CES}	70	V
Emitter-Base Voltage	V _{EBO}	3.0	V
Collector Current (Peak)	Ι _C	1.6	А
Power Dissipation @ +25°C	P _{TOT}	50	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	TJ	200	°C

Electrical Specifications: T_c = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Мах	Units
Collector-Emitter Breakdown Voltage	I _C = 25mA		BV _{CES}	60	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40V$		I _{CES}	-	2.5	mA
Thermal Resistance	Vcc = 28V, Pout = 25W	F = 1.2, 1.3, 1.4 GHz	R _{TH(JC)}	-	3.6	°C/W
Output Power	Vcc = 28V, Pout = 25W	F = 1.2, 1.3, 1.4 GHz	P _{IN}	-	2.8	W
Power Gain	Vcc = 28V, Pout = 25W	F = 1.2, 1.3, 1.4 GHz	G _P	9.5	-	dB
Collector Efficiency	Vcc = 28V, Pout = 25W	F = 1.2, 1.3, 1.4 GHz	η _c	50	-	%
Input Return Loss	Vcc = 28V, Pout = 25W	F = 1.2, 1.3, 1.4 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 28V, Pout = 25W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	3:1	-
Load Mismatch Stability	Vcc = 28V, Pout = 25W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

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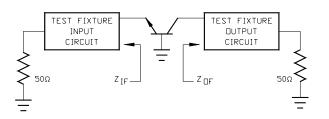


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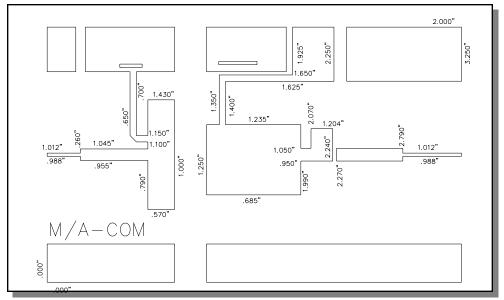
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RF Test Fixture Impedance

F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1.2	2.1 - j4.5	3.7 + j0.9
1.3	2.1 - j3.9	3.6 + j0.4
1.4	2.2 - j3.4	3.0 + j0.2

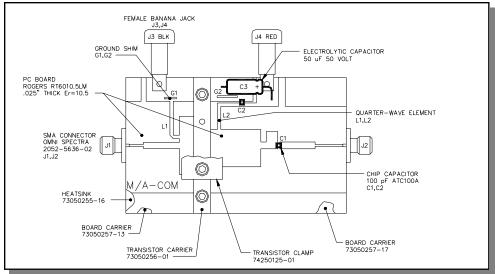


Test Fixture Circuit Dimensions



Test Fixture Assembly

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